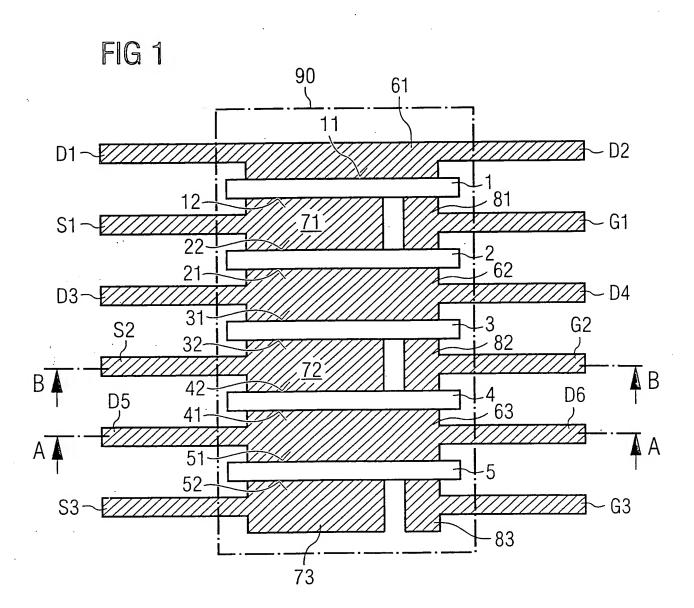
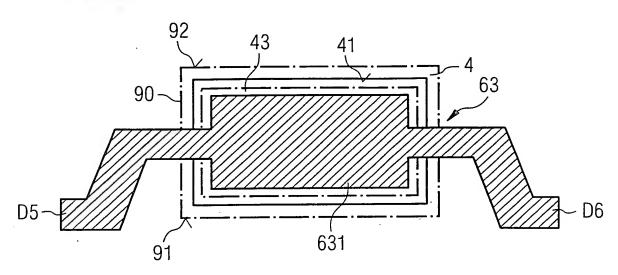
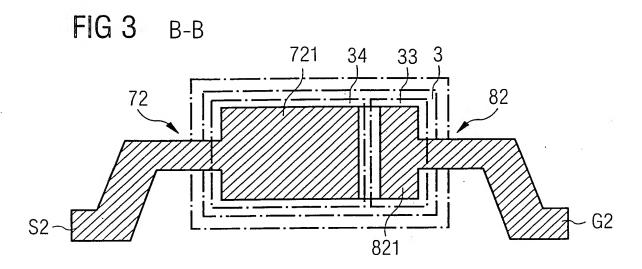
Docket No. 1FT979US/I434.102.101 SEMICONDUCTOR COMPONENT HAVING AT LEAST TWO CHIPS WHICH ARE INTEGRATED IN A HOUSING AND WITH WHICH CONTACT IS MADE BY A COMMON CONTACT CHIP Ralf Otremba 1/5



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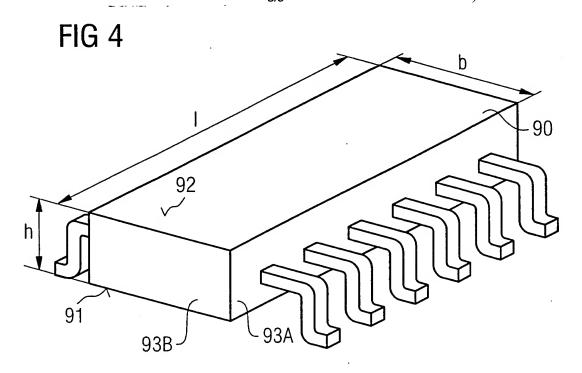
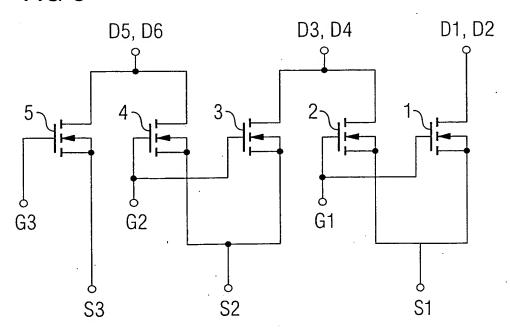
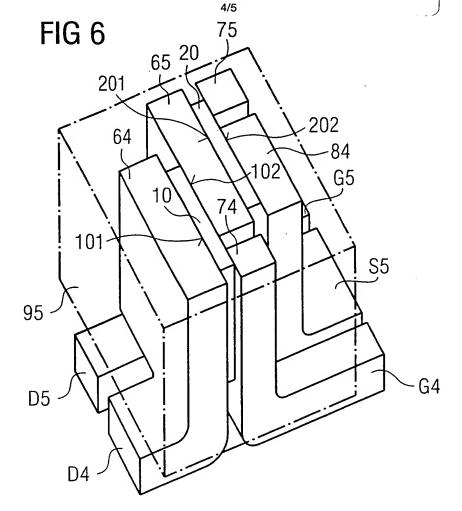
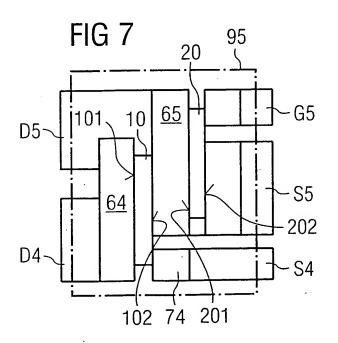


FIG 5



Docket No. 1FT979US/I434.102.101
SEMICONDUCTOR COMPONENT HAVING AT LEAST TWO
CHIPS WHICH ARE INTEGRATED IN A HOUSING AND WITH
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5/5

